Optoelectronics and Plasmonics with hBN-Encapsulated Graphene

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The creation of ultraclean heterostructures in which graphene is encapsulated by hBN enables reaching the regime of intrinsic properties, such as room-temperature mobility exceeding 10⁵ cm²/Vs [1]. This talk will first review our efforts (with Enalund, MIT and others) to explore the potential of hBNencapsulated graphene for optoelectronic devices. These include high performance photodetectors [2], modulators [3], and thermal emitters [4]. Recent work exploring the speed and sensitivity limits of these structures will be discussed. In collaboration with Koppens and Hillenbrand (ICFO) and Basov (UCSD) we have likewise explored the potential for improved performance and new phenomena in graphene plasmonics [5]. This includes photo-induced phenomena [6], and thermoelectric detection of plasmons [7,8,9]

References

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Figure 1: Optoelectronic structures. (left), high-frequency modulator. (right) thermal light emitter.



Figure 2: Thermoelectric detection of plasmon resonances in a graphene p-n junction structure